

# Nanostack Impuls-Laserdiode im Plastikgehäuse 75 W Spitzenleistung

## Nanostack Pulsed Laser Diode in Plastic Package 75 W Peak Power

### SPL PL90\_3



#### Besondere Merkmale

- Kostengünstiges Plastikgehäuse
- Zuverlässiges InGaAs/GaAs kompressiv verspanntes Halbleiter-Material
- Hochleistungslaser mit „Large-Optical-Cavity“ (LOC) Struktur für ein schmales Fernfeld
- Nanostack Lasertechnologie beinhaltet mehrere epitaktisch integrierte Emittoren
- Austrittsöffnung  $200 \mu\text{m} \times 10 \mu\text{m}$

#### Anwendungen

- Entfernungsmessung
- Sicherheit, Überwachung
- Beleuchtung, Zündung
- Test- und Messsysteme

#### Sicherheitshinweise

Je nach Betriebsart emittieren diese Bauteile hochkonzentrierte, nicht sichtbare Infrarot-Strahlung, die gefährlich für das menschliche Auge sein kann. Produkte, die diese Bauteile enthalten, müssen gemäß den Sicherheitsrichtlinien der IEC-Norm 60825-1 behandelt werden.

#### Features

- Low cost plastic package
- Reliable strained InGaAs/GaAs material
- High power large-optical-cavity (LOC) structure for a narrow far-field
- Nanostack laser technology including multiple epitaxially stacked emitters
- Laser aperture  $200 \mu\text{m} \times 10 \mu\text{m}$

#### Applications

- Range finding
- Security, surveillance
- Illumination, ignition
- Test and measurement systems

#### Safety Advices

Depending on the mode of operation, these devices emit highly concentrated non visible infrared light which can be hazardous to the human eye. Products which incorporate these devices have to follow the safety precautions given in IEC 60825-1 “Safety of laser products”

Typ	Emitteranzahl	Opt. Spitzenausgangsleistung Opt. Peak Power	Wellenlänge	Bestellnummer Ordering Code
Type	Number of Emitters		Wavelength	
SPL PL90_3	3	75 W	905 nm	Q62702P5353

**Grenzwerte (kurzzeitiger Betrieb) ( $T_A = 25^\circ\text{C}$ )**  
**Maximum Ratings (short time operation)**

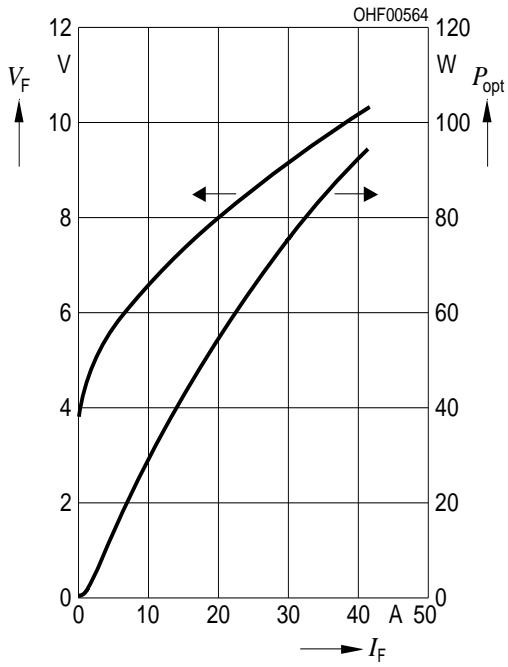
Parameter Parameter	Symbol Symbol	Werte Values		Einheit Unit
		min.	max.	
Spitzenausgangsleistung Peak output power	$P_{\text{peak}}$	—	90	W
Spitzendurchlaßstrom Peak forward current	$I_F$	—	40	A
Pulsbreite (Halbwertsbreite) Pulse width (FWHM)	$t_p$	—	100	ns
Tastverhältnis Duty cycle	d.c.	—	0.1	%
Sperrspannung Reverse voltage	$V_R$	—	3	V
Betriebstemperatur Operating temperature	$T_{\text{op}}$	-40	+ 85	°C
Lagertemperatur Storage temperature	$T_{\text{stg}}$	-40	+ 100	°C
Löttemperatur ( $t_{\text{max}} = 10$ s, 2 mm von Gehäuseunterseite) Soldering temperature ( $t_{\text{max}} = 10$ s, 2 mm from bottom edge of case)	$T_s$	—	+ 260	°C

**Optische Kennwerte ( $T_A = 25^\circ\text{C}$ )**  
**Optical Characteristics**

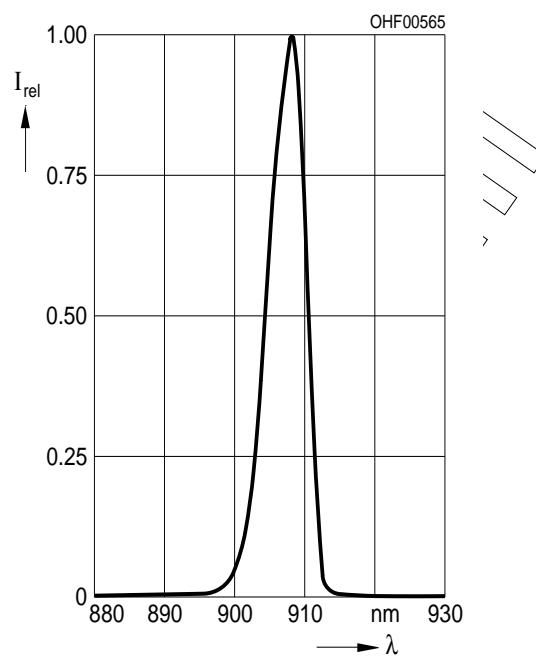
Parameter Parameter	Symbol Symbol	Werte Values			Einheit Unit
		min.	typ.	max.	
Zentrale Emissionswellenlänge <sup>1)</sup> Emission wavelength <sup>1)</sup>	$\lambda_{\text{peak}}$	895	905	915	nm
Spektralbreite (Halbwertsbreite) <sup>1)</sup> Spectral width (FWHM) <sup>1)</sup>	$\Delta\lambda$	–	7	–	nm
Spitzenausgangsleistung <sup>1)</sup> Peak output power <sup>1)</sup>	$P_{\text{op}}$	65	75	85	W
Schwellstrom Threshold current	$I_{\text{th}}$	0.5	0.75	1.0	A
Betriebsspannung <sup>1)</sup> Operating voltage <sup>1)</sup>	$V_{\text{op}}$	8	9	11	V
Minimale Anstiegs- und Abfallzeit (10% ... 90%) Minimum rise and fall time (10% ... 90%)	$t_r, t_f$	–	1	–	ns
Austrittsöffnung Aperture size	$w \times h$	200 × 10	–	–	μm
Strahldivergenz (Halbwertsbreite) Beam divergence (FWHM)	$\theta_{  } \times \theta_{\perp}$	–	11° × 25°	–	Grad deg.
Temperaturkoeffizient der Wellenlänge Temperature coefficient of wavelength	$\partial\lambda / \partial T$	–	0.28	–	nm/K
Temperaturkoeffizient der opt. Ausgangsleistung Temperature coefficient of optical power	$\partial P_{\text{op}} / P_{\text{op}} \partial T$	–	-0.4	–	%/K
Thermischer Widerstand Thermal resistance	$R_{\text{th JS}}$	–	160	–	K/W

<sup>1)</sup> Standardbetriebsbedingungen beziehen sich auf eine Pulsbreite von 100 ns bei einer Frequenz von 1 kHz und einem Betriebsstrom von 30 A bei  $T_A = 25^\circ\text{C}$ .  
 Standard operating conditions refer to pulses of 100 ns pulse width at 1 kHz rate with 30 A operating current at  $T_A = 25^\circ\text{C}$ .

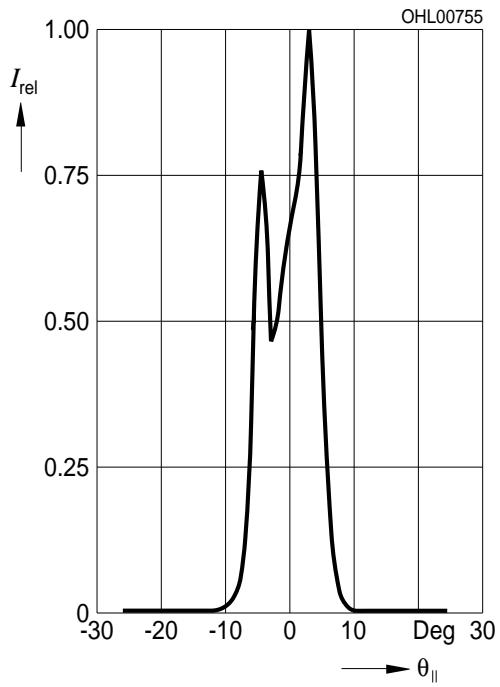
**Optical output power  $P_{\text{opt}}$  and forward voltage  $V_F$  vs. forward current  $I_F$  ( $T_A = 25^\circ \text{C}$ )**



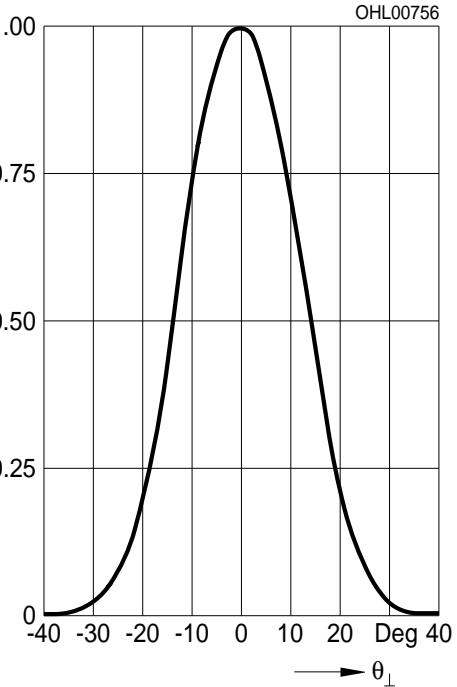
**Optical spectrum, relative intensity  $I_{\text{rel}}$  vs. wavelength  $\lambda$  ( $T_A = 25^\circ \text{C}$ ,  $P_{\text{opt}} = 75 \text{ W}$ )**



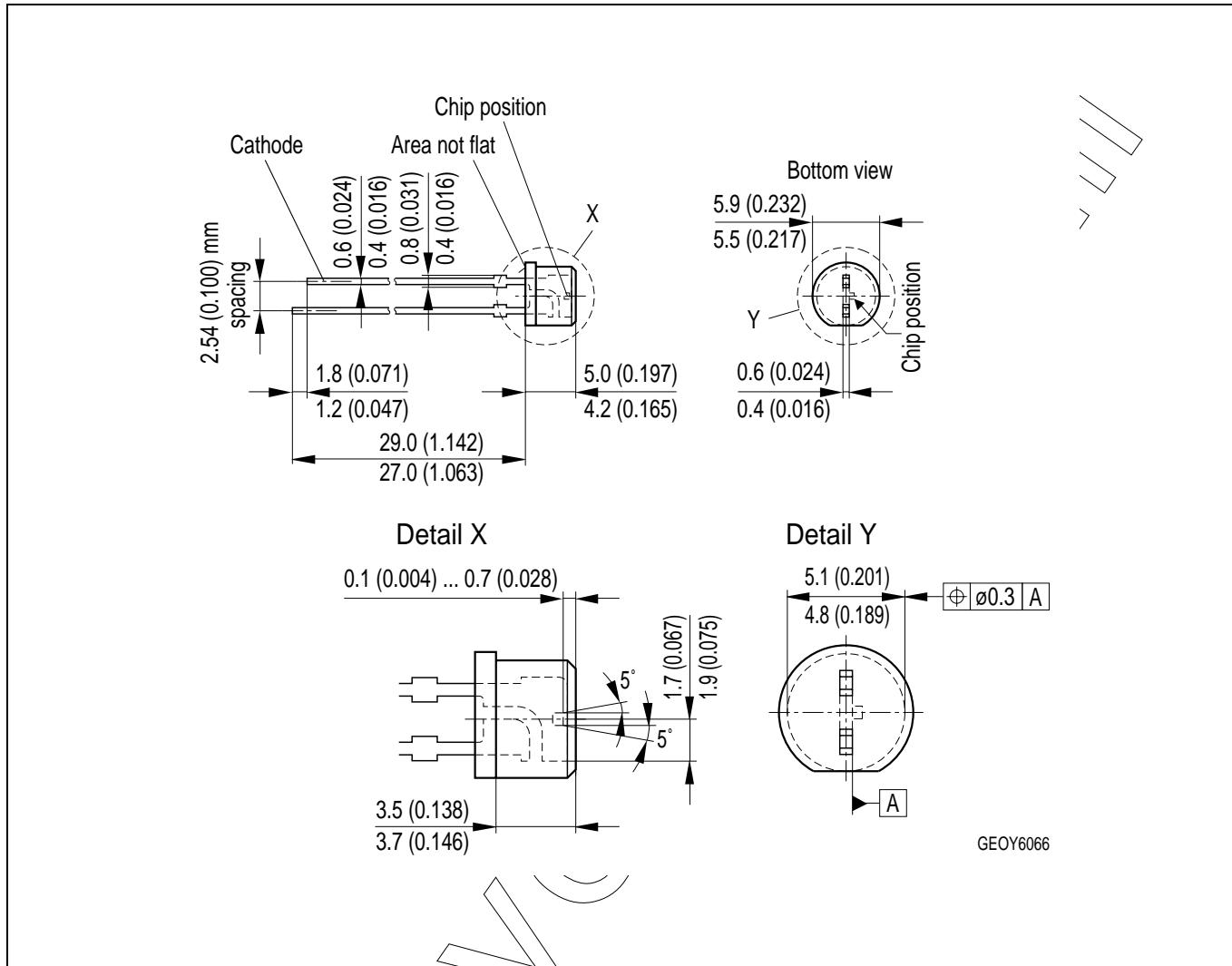
**Far-field distribution parallel to junction  $I_{\text{rel}}$  vs.  $\theta_{\parallel}$  ( $T_A = 25^\circ \text{C}$ ,  $P_{\text{opt}} = 75 \text{ W}$ )**



**Far-field distribution perpendicular to junction  $I_{\text{rel}}$  vs.  $\theta_{\perp}$  ( $T_A = 25^\circ \text{C}$ ,  $P_{\text{opt}} = 75 \text{ W}$ )**



**Maßzeichnung**  
**Package Outlines**



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

W W W W W

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